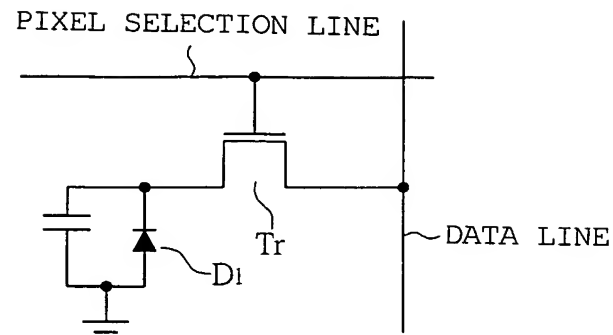


*FIG. 1*



*FIG. 2*

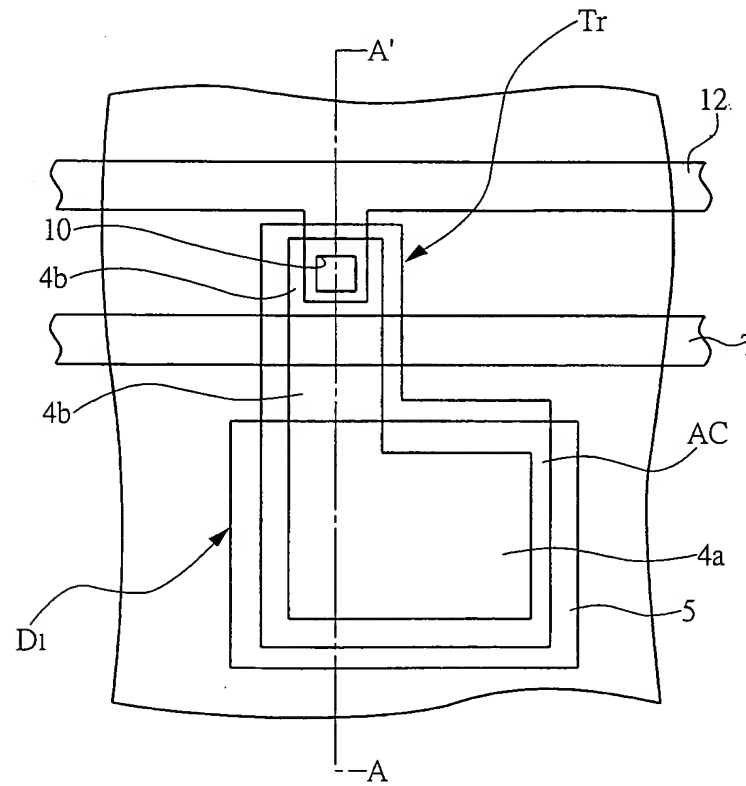


FIG. 3

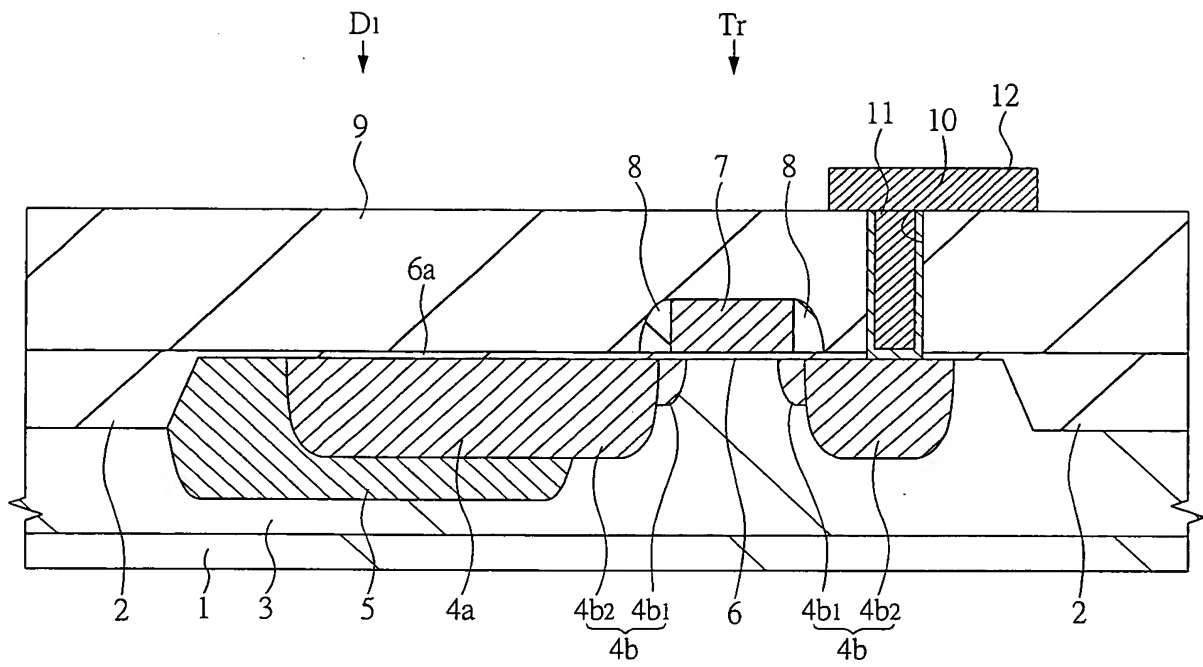


FIG. 4

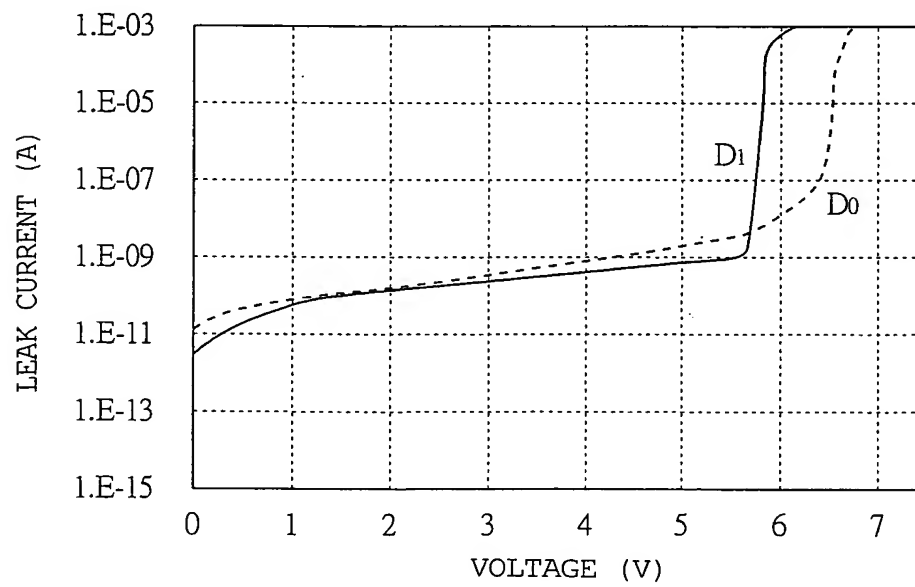


FIG. 5

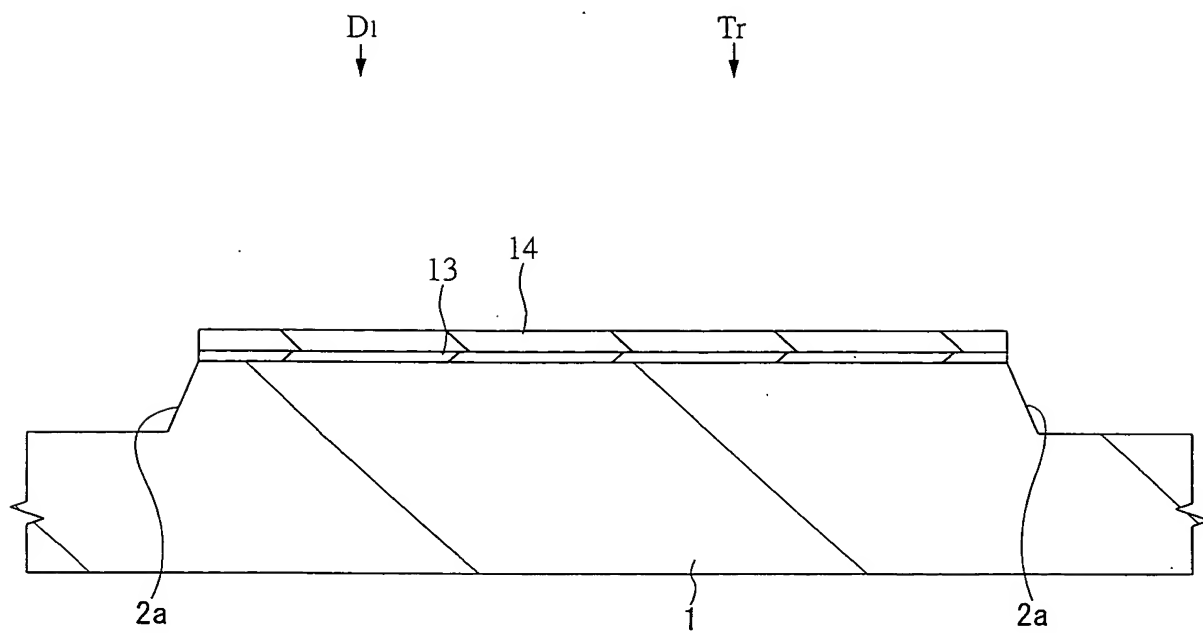


FIG. 6

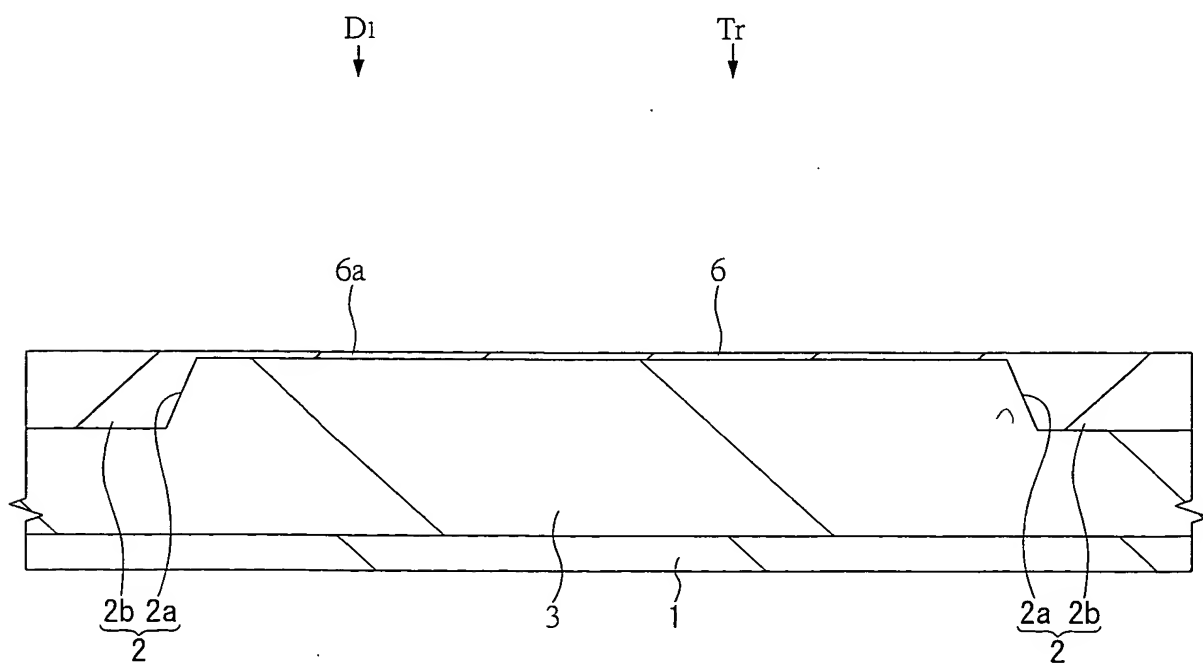


FIG. 7

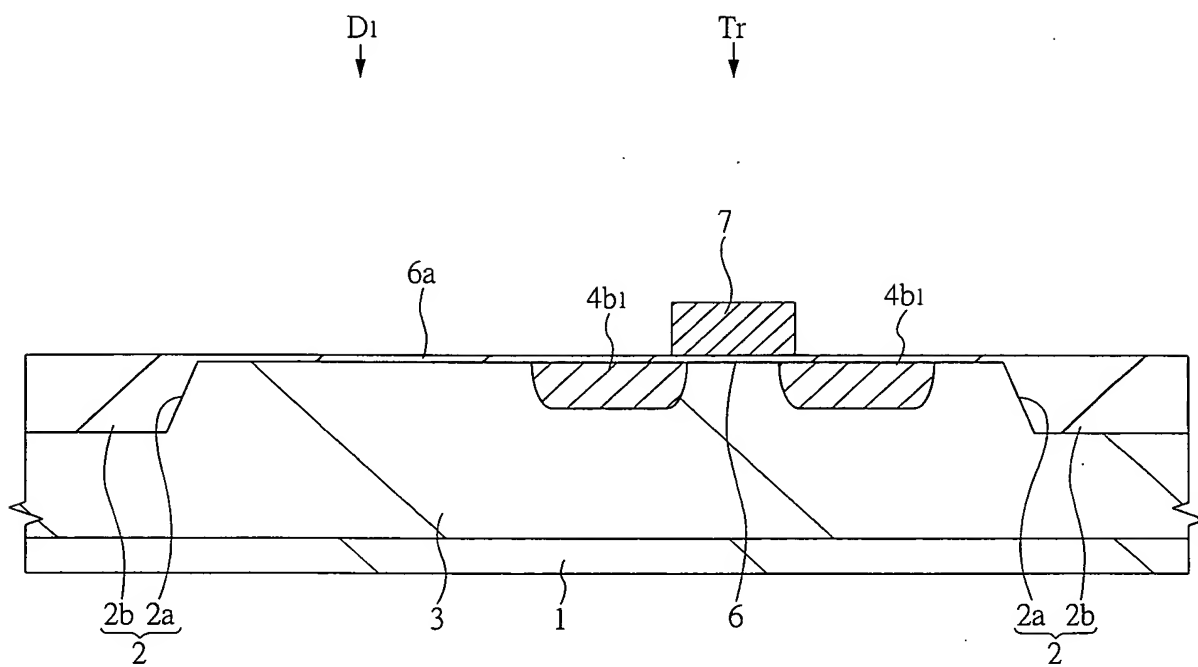
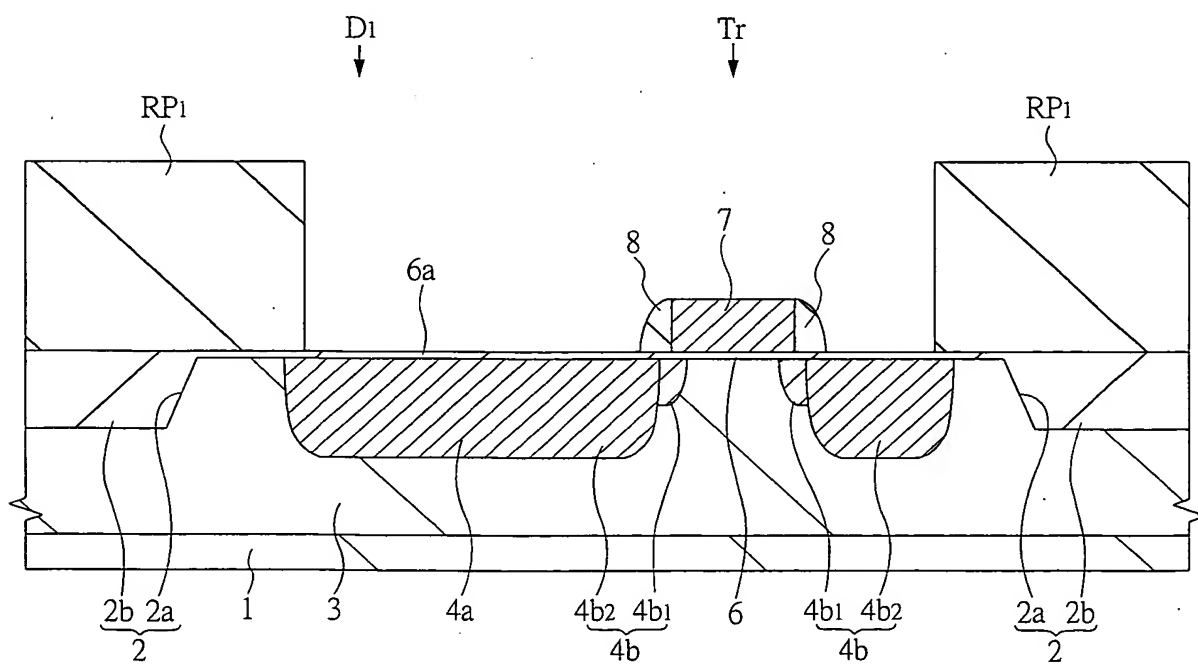


FIG. 8



A cross-sectional view of a semiconductor device. The device consists of a substrate (1) with a trench (3) and a raised portion (7). The trench (3) contains a conductive layer (2a) and a dielectric layer (2b). The raised portion (7) contains a conductive layer (7) and a dielectric layer (8). A dashed line indicates a cross-section through the device. Labels include D1, Tr, RP2, 6a, 8, 7, 2b, 2a, 1, 3, 5, 4a, 4b2, 4b1, 6, 4b1, 4b2, 2a, and 2b.

[illegible]

*FIG. 11*

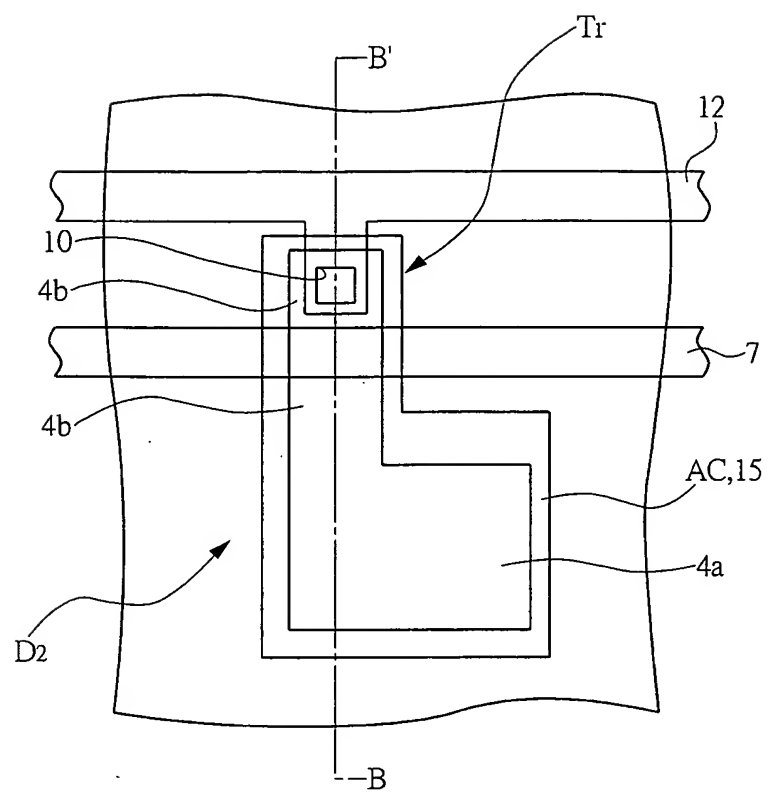
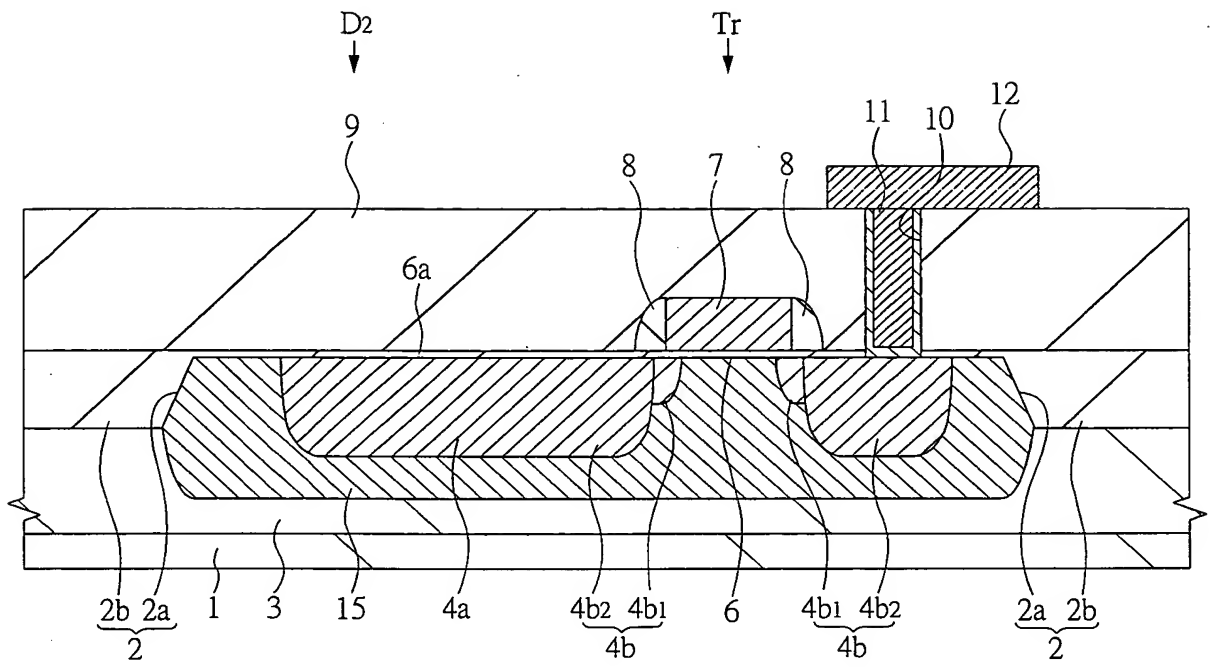


FIG. 12



[illegible]